

This is a repository copy of *XPS and XMCD study of Fe₃O₄/GaAs interface*.

White Rose Research Online URL for this paper:

<https://eprints.whiterose.ac.uk/id/eprint/1846/>

Article:

Lu, Y X, Claydon, J S, Ahmad, E et al. (4 more authors) (2005) XPS and XMCD study of Fe₃O₄/GaAs interface. IEEE Transactions on Magnetics. pp. 2808-2810. ISSN: 1941-0069

<https://doi.org/10.1109/TMAG.2005.854834>

Reuse

Items deposited in White Rose Research Online are protected by copyright, with all rights reserved unless indicated otherwise. They may be downloaded and/or printed for private study, or other acts as permitted by national copyright laws. The publisher or other rights holders may allow further reproduction and re-use of the full text version. This is indicated by the licence information on the White Rose Research Online record for the item.

Takedown

If you consider content in White Rose Research Online to be in breach of UK law, please notify us by emailing eprints@whiterose.ac.uk including the URL of the record and the reason for the withdrawal request.

XPS and XMCD Study of $\text{Fe}_3\text{O}_4/\text{GaAs}$ Interface

Yongxiong Lu¹, Jill S. Claydon¹, Ehsan Ahmad¹, Yongbing Xu¹, Sarah M. Thompson², Karen Wilson³, and Gerrit van der Laan⁴

¹Spintronics Laboratory, Department of Electronics, The University of York, York, YO10 5DD, U.K.

²Department of Physics, The University of York, York, YO10 5DD, U.K.

³Department of Chemistry, The University of York, York, YO10 5DD, U.K.

⁴Daresbury Laboratory, Warrington, WA4 4AD, U.K.

Ultrathin Fe oxide films of various thicknesses prepared by post-growth oxidation on GaAs(100) surface have been investigated with X-ray photoelectron spectroscopy (XPS), X-ray absorption spectroscopy (XAS), and X-ray magnetic circular dichroism (XMCD). The XPS confirms that the surfaces of the oxide are Fe_3O_4 rather than Fe_2O_3 . XAS and XMCD measurements indicate the presence of insulating Fe divalent oxide phases (FeO) beneath the surface Fe_3O_4 layer with the sample thickness above 4 nm. This FeO might act as a barrier for the spin injection into the GaAs.

Index Terms—Half-metallic Fe_3O_4 , post-growth oxidation, spintronics, XMCD.

I. INTRODUCTION

HALF-METALLIC Oxide Fe_3O_4 (magnetite) is one of the most promising materials for spintronic applications as it has high Curie temperature and large spin polarization at the Fermi level [1], [2]. For example, magnetite has been used as electrode material in magnetic junctions [3], [4]. To inject spin into semiconductors, such as GaAs, synthesis of $\text{Fe}_3\text{O}_4/\text{GaAs}$ half-metal/semiconductor hybrid structure is essential. However, to inject spin into semiconductors, the electron diffusion method has proved to be less efficient compared with electron tunneling method, where there is a barrier between the spin injection source and the semiconductor [5], [6]. Previously, Fe divalent oxide, namely FeO, has been found to be an insulator with band gaps of 1.3 and 2.2 eV for the Fe 3d/O 2sp-Fe 4s and Fe 3d/O 2sp-Fe 3d transitions, respectively [7], [8]. So an interesting problem arises: can we achieve a spin tunneling hybrid structure with an insulator layer between the half-metallic Fe_3O_4 and the semiconductor GaAs?

We have demonstrated in our previous work that an ultrathin Fe film on GaAs can be oxidized into Fe_3O_4 by post-growth oxidation [9]. In this paper, we present our work on the surface and interface of the Fe oxide/GaAs(100) hybrid structure using X-ray spectroscopy techniques, namely X-ray photoelectron spectroscopy (XPS), X-ray absorption spectroscopy (XAS) and X-ray magnetic circular dichroism (XMCD). A series of samples with nominal Fe thickness of 2, 3, 4, and 6 nm were prepared by post-growth oxidation. The thickness dependencies of the interface magnetic properties and chemical composition have been investigated.

II. EXPERIMENT

The samples were prepared by post-growth oxidation of ultrathin Fe films on GaAs. After wet etching by $\text{H}_2\text{SO}_4:\text{H}_2\text{O}_2:\text{H}_2\text{O}$ (4:1:1) solution, the GaAs(100) substrates were loaded into a molecular beam epitaxy (MBE) chamber. A thermal annealing

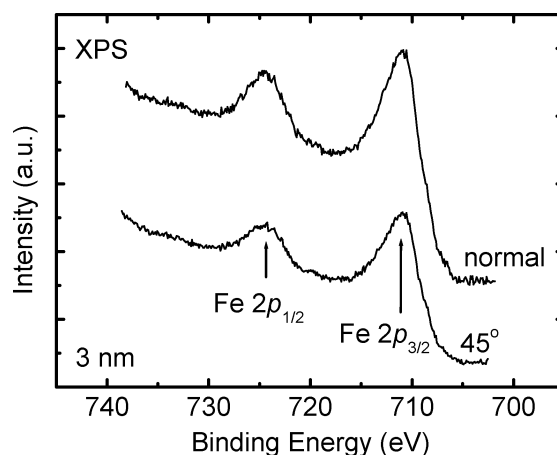


Fig. 1. Fe 2p XPS measurements of the 3-nm sample with the sample surface normal or 45° tilted to the incident X-ray. The geometries are labeled. Both spectra show widened peaks and no shake-up satellite can be identified.

at 800 K about 40 min followed, prior to the Fe growth. The Fe was then evaporated from a crucible, at a distance of 400 mm away from the fixed GaAs substrate. The growth rate was monitored by a quartz microbalance and set to 2 Å/min. After Fe growth, the samples were oxidized in an O_2 environment with a partial pressure of 5×10^{-5} mbar, and at a temperature of 500 K for 5 to 10 min, until a stable reflection high-energy electron diffraction (RHEED) pattern has been achieved.

The XPS measurements were done with Mg K α radiation. The XMCD measurements were carried out in the station 1.1 of the Synchrotron Radiation Source at Daresbury Laboratory (U.K.). The resulting current output from the sample was measured in total electron yield mode as a function of the X-ray photon energy. The dichroism was obtained as the difference spectrum, $I^+ - I^-$, achieved by reversing the direction of the applied magnetic field at fixed polarization.

III. RESULTS AND DISCUSSION

Plotted in Fig. 1 are the XPS measurements of the 3-nm sample, at normal and 45° incident angles with respect to the surface. In Fe_2O_3 , the Fe atoms are completely oxidized

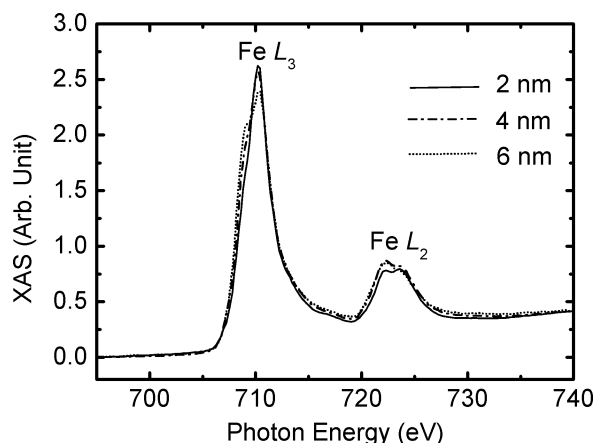


Fig. 2. XAS measurements with thickness dependency. The start and end points of the 4- and 6-nm spectra have been normalized to the 2-nm spectrum for better comparison.

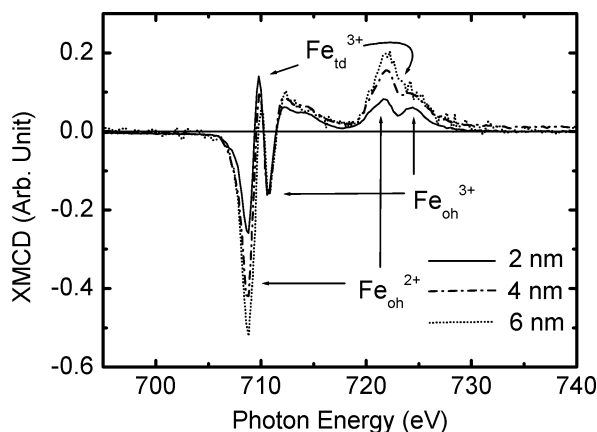


Fig. 3. XMCD spectra illustrating thickness dependency of the dichroism on the photon energy. The intensities are normalized to the $\text{Fe}_{\text{oh}}^{3+}$ peaks and the photon energies are shifted to the same position. The peaks from different chemical compositions are deduced from relative photon energies.

into trivalent Fe cations, generating narrower peaks in the XPS compared to Fe_3O_4 , which consists of both divalent and trivalent Fe cations. Fe_2O_3 also features its XPS spectra with shake-up satellite peaks between the main peaks [10]. From the widened and shake-up satellite-free spectra in Fig. 1, it is clear that the sample composition is Fe_3O_4 rather than Fe_2O_3 , which cannot be differentiated by the RHEED patterns during growth. It is worth noting that there is little difference between the two measurement geometries, normal or tilted 45° to the surface of the sample, suggesting a uniform composition for the 3-nm sample since the two measurement geometries have different penetration depths in the sample.

Fig. 2 illustrates the thickness dependencies of the XAS measurements. For the 2-nm thick sample, both Fe L_2 and Fe L_3 edges show clearly different chemical states which comes from the Fe_3O_4 in the sample. While at the lower energy edge for the 6-nm film, a strong peak distorts the Fe L_3 edge absorption. This may be due to the presence of more Fe^{2+} cations, rather than ferromagnetic atomic Fe atoms in the 6-nm film, as discussed below.

In Fig. 3 the XMCD dependencies are depicted, with their peak intensities normalized to the $\text{Fe}_{\text{oh}}^{3+}$ (octahedral) peaks and

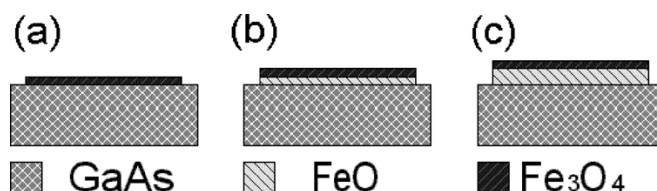


Fig. 4. Sketches of the proposed layered oxide films. (a) Surface layer with total thickness under 3 nm is Fe_3O_4 . (b) FeO appears when the thickness achieved 4 nm. (c) FeO thickness increases upon the increasing total thickness, while the surface Fe_3O_4 thickness keeps constant.

the positions of the $\text{Fe}_{\text{oh}}^{3+}$ peaks are shift to the same energy. The chemical states of the peaks are deduced from the relative photon energy. Interestingly the $\text{Fe}_{\text{oh}}^{2+}$ (octahedral) peaks have an increasing strength, while the $\text{Fe}_{\text{td}}^{3+}$ peaks show a reduced strength upon increasing thickness. This decrease in the strength of the $\text{Fe}_{\text{td}}^{3+}$ (tetrahedral) peak can be explained by the increase of the $\text{Fe}_{\text{oh}}^{2+}$ strength, which has an inversed strength compared with that of the $\text{Fe}_{\text{td}}^{3+}$ in the XMCD. Hence, a constant $\text{Fe}_{\text{td}}^{3+}:\text{Fe}_{\text{oh}}^{3+}$ ratio is found on the surface of the oxide film upon increasing total thickness, taking the counteraction effect into account. Then we come to the conclusion that the surface area of the oxide is still Fe_3O_4 , as also suggested by XPS measurements.

The increasing intensity of the $\text{Fe}_{\text{oh}}^{2+}$ peaks is intriguing. In the oxidation of Fe film, below the top Fe_3O_4 , atomic Fe was previously found. That is, a $\text{Fe}_3\text{O}_4/\text{Fe}$ structure might be achieved by low-temperature oxidation [11]. The Fe-O phase diagram also indicates this structure [12]. Since the atomic Fe and divalent Fe cations have different chemical environments, their energy positions on the XMCD spectrum can not be identical. However, In Fig. 3, in which the spectra are calibrated using the $\text{Fe}_{\text{oh}}^{3+}$ position, all the Fe^{2+} peaks remain at the same energy position despite the increasing intensity with increasing thickness. From both Figs. 2 and 3, it can be concluded that there are more partially oxidized Fe cations (divalent Fe cations) in the sample than the Fe_3O_4 when the thickness achieves 4 nm, and no atomic Fe was identified.

There are two possibilities for the extra Fe divalent cations. First, the sample is not uniform, and the chemical stoichiometry varies upon the depth from the surface to the oxide/GaAs interface. The second possibility is that there is a FeO layer below the surface Fe_3O_4 layer, whereas the surface Fe_3O_4 thicknesses keep constant. When the total thickness increases, once oxidized, the FeO thickness increases. Since the surface is Fe_3O_4 , which has a defined quota of the Fe^{2+} cations, the extra partially oxidized Fe^{2+} cations are believed to present under the Fe_3O_4 layer. That is, more Fe^{2+} cations are generated near the oxide/GaAs interface when the total thickness increases, as indicated by Fig. 2. This possibility is supported by the oxidation mechanism [12]. Namely, a layered structure might be present in the oxide, as illustrated in Fig. 4. However, we would like to note that interfacial oxygen defects might form at the interface. These defects would be detrimental to the half-metallicity of Fe_3O_4 and efficient spin injection into GaAs. Further investigation such as high resolution transmission electron microscopy (HR-TEM) is needed.

IV. CONCLUSION

In summary, for the sample thickness below 3 nm, a uniform Fe_3O_4 has been formed on the GaAs(100), constituting a Fe_3O_4 oxide/semiconductor hybrid structure. For the thickness above 4 nm, there is an insulating FeO layer beneath the Fe_3O_4 near the interface and this insulating FeO layer might be a useful tunneling barrier for high efficiency spin injection into GaAs.

ACKNOWLEDGMENT

This work was supported in part by the White Rose Scholarship.

REFERENCES

- [1] J. M. D. Coey and C. L. Chien, "Half-metallic ferromagnetic oxides," *MRS Bulletin*, vol. 28, pp. 720–724, 2003.
- [2] S. von Molnar and D. Read, "New materials for semiconductor spin-electronics," *Proc. IEEE*, vol. 91, no. 5, pp. 715–726, May 2003.
- [3] R. V. Chopdekar, G. Hu, A. C. Ford, and Y. Suzuki, "Magnetotransport in exchange-coupled magnetite junctions," *IEEE Trans. Magn.*, vol. 40, no. 4, pp. 2302–2304, Jul. 2004.
- [4] S. Cardoso, Z. Zhang, H. Li, R. Ferreira, P. Freitas, J. C. Soares, E. Snoeck, and X. Batlle, "Characterization of nano-oxide layers fabricated by ion beam oxidation," *IEEE Trans. Magn.*, vol. 38, no. 5, pp. 2755–2757, Sep. 2002.
- [5] J. F. Gregg, R. P. Borges, E. Jouguelet, C. L. Dennis, I. Petej, S. M. Thompson, and K. Ounadjela, "Spin injection efficiency in spin electronic devices," *J. Magn. Magn. Mater.*, vol. 265, pp. 274–289, 2003.
- [6] G. Schmidt, D. Ferrand, L. W. Molenkamp, A. T. Filip, and B. J. van Wees, "Fundamental obstacle for electrical spin injection from a ferromagnetic metal into a diffusive semiconductor," *Phys. Rev. B*, vol. 62, pp. R4790–R4793, Aug. 2000.
- [7] M. Alfredsson, G. D. Price, C. R. A. Catlow, S. C. Parker, R. Orlando, and J. P. Brodholt, "Electronic structure of the antiferromagnetic B1-structured FeO," *Phys. Rev. B*, vol. 70, pp. 165 111–165 116, Oct. 2004.
- [8] I. I. Mazin and V. I. Anisimov, "Insulating gap in FeO: Correlations and covalency," *Phys. Rev. B*, vol. 55, pp. 12 822–12 825, May 1997.
- [9] Y. X. Lu, J. S. Claydon, Y. B. Xu, S. M. Thompson, K. Wilson, and G. van der Laan, "Epitaxial growth and magnetic properties of half-metallic Fe_3O_4 on GaAs(100)," *Phys. Rev. B*, vol. 70, pp. 23 3304–23 3307, Dec. 2004.
- [10] Y. Gao and S. A. Chambers, "Heteroepitaxial growth of $-\text{Fe}_2\text{O}_3$, $-\text{Fe}_3\text{O}_4$, and Fe_3O_4 thin films by oxygen-plasma-assisted molecular beam epitaxy," *J. Cryst. Growth*, vol. 174, pp. 446–454, May 1996.
- [11] H.-J. Kim, J.-H. Park, and E. Vescovo, "Oxidation of the Fe(110) surface: An Fe_3O_4 (111)/Fe(110) bilayer," *Phys. Rev. B*, vol. 61, pp. 15 284–15 287, Jun. 2000.
- [12] O. Kubaschewski and B. E. Hopkins, *Oxidation of Metals and Alloys*, 2nd ed. London, U.K.: Butterworth, 1967.

Manuscript received February 6, 2005.